

DATA SHEET

BUW11F; BUW11AF Silicon diffused power transistors

Product specification
Supersedes data of February 1996
File under Discrete Semiconductors, SC06

1997 Aug 14

Silicon diffused power transistors

BUW11F; BUW11AF

DESCRIPTION

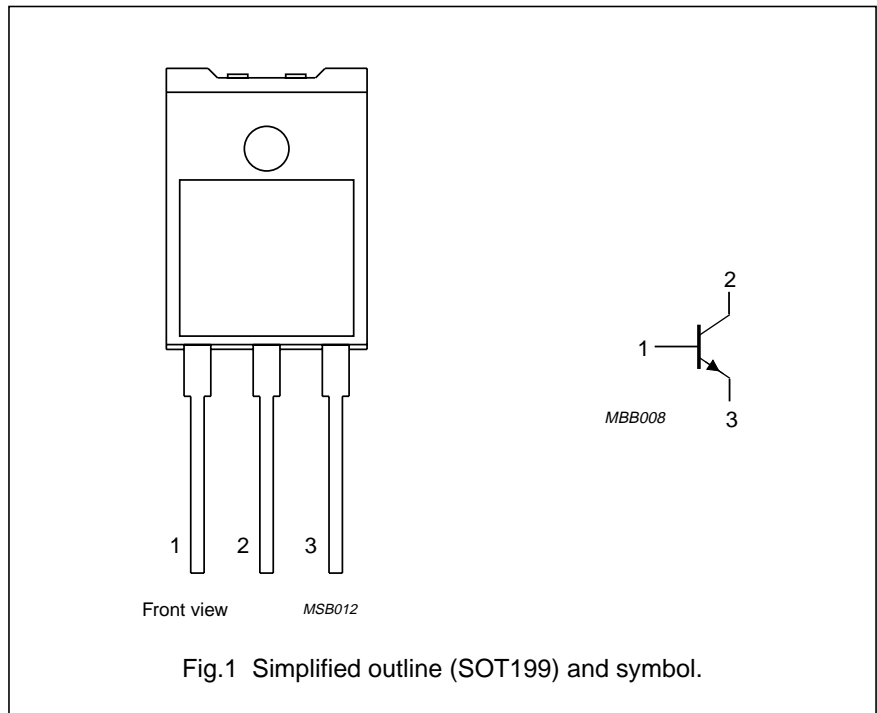
High-voltage, high-speed, glass-passivated NPN power transistor in a SOT199 package.

APPLICATIONS

- Converters
- Inverters
- Switching regulators
- Motor control systems.

PINNING

| PIN | DESCRIPTION |
|-----|--------------------------------------|
| 1 | base |
| 2 | collector |
| 3 | emitter |
| mb | mounting base; electrically isolated |



QUICK REFERENCE DATA

| SYMBOL | PARAMETER | CONDITIONS | MAX. | UNIT |
|-------------|--------------------------------------|----------------------------------|------|---------|
| V_{CESM} | collector-emitter peak voltage | $V_{BE} = 0$ | 850 | V |
| | BUW11F | | | |
| V_{CEO} | collector-emitter voltage | open base | 400 | V |
| | BUW11AF | | | |
| V_{CEsat} | collector-emitter saturation voltage | | 1.5 | V |
| I_{Csat} | collector saturation current | | 3 | A |
| | BUW11AF | | | |
| I_C | collector current (DC) | see Figs 2 and 4 | 5 | A |
| I_{CM} | collector current (peak value) | $t_p < 20$ ms; see Fig.2 | 10 | A |
| P_{tot} | total power dissipation | $T_h \leq 25$ °C; see Fig.3 | 32 | W |
| t_f | fall time | resistive load; see Figs 8 and 9 | 0.8 | μ s |

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THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|---------------|---|------------|-------|------|
| $R_{th\ j-h}$ | thermal resistance from junction to external heatsink | note 1 | 3.95 | K/W |
| | | note 2 | 3.05 | K/W |
| $R_{th\ j-a}$ | thermal resistance from junction to ambient | | 35 | K/W |

Notes

1. Mounted **without** heatsink compound and 30 ± 5 N force on centre of package.
2. Mounted **with** heatsink compound and 30 ± 5 N force on centre of package.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|------------|---|-------------------------------------|------|------|------|
| V_{CESM} | collector-emitter peak voltage BUW11F BUW11AF | $V_{BE} = 0$ | – | 850 | V |
| | | | – | 1000 | V |
| V_{CEO} | collector-emitter voltage BUW11F BUW11AF | open base | – | 400 | V |
| | | | – | 450 | V |
| I_{Csat} | collector saturation current BUW11F BUW11AF | | – | 3 | A |
| | | | – | 2.5 | A |
| I_C | collector current (DC) | see Figs 2 and 4 | – | 5 | A |
| I_{CM} | collector current (peak value) | $t_p < 20$ ms; see Fig.2 | – | 10 | A |
| I_B | base current (DC) | | – | 2 | A |
| I_{BM} | base current (peak value) | $t_p < 20$ ms | – | 4 | A |
| P_{tot} | total power dissipation | $T_h \leq 25$ °C; see Fig.3; note 1 | – | 32 | W |
| | | $T_h \leq 25$ °C; see Fig.3; note 2 | – | 41 | W |
| T_{stg} | storage temperature | | –65 | +150 | °C |
| T_j | junction temperature | | – | 150 | °C |

Notes

1. Mounted **without** heatsink compound and 30 ± 5 N force on centre of package.
2. Mounted **with** heatsink compound and 30 ± 5 N force on centre of package.

ISOLATION CHARACTERISTICS

| SYMBOL | PARAMETER | TYP. | MAX. | UNIT |
|-------------|--|------|------|------|
| V_{isolM} | isolation voltage from all terminals to external heatsink (peak value) | – | 1500 | V |
| C_{isol} | isolation capacitance from collector to external heatsink | – | 21 | pF |

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CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified.

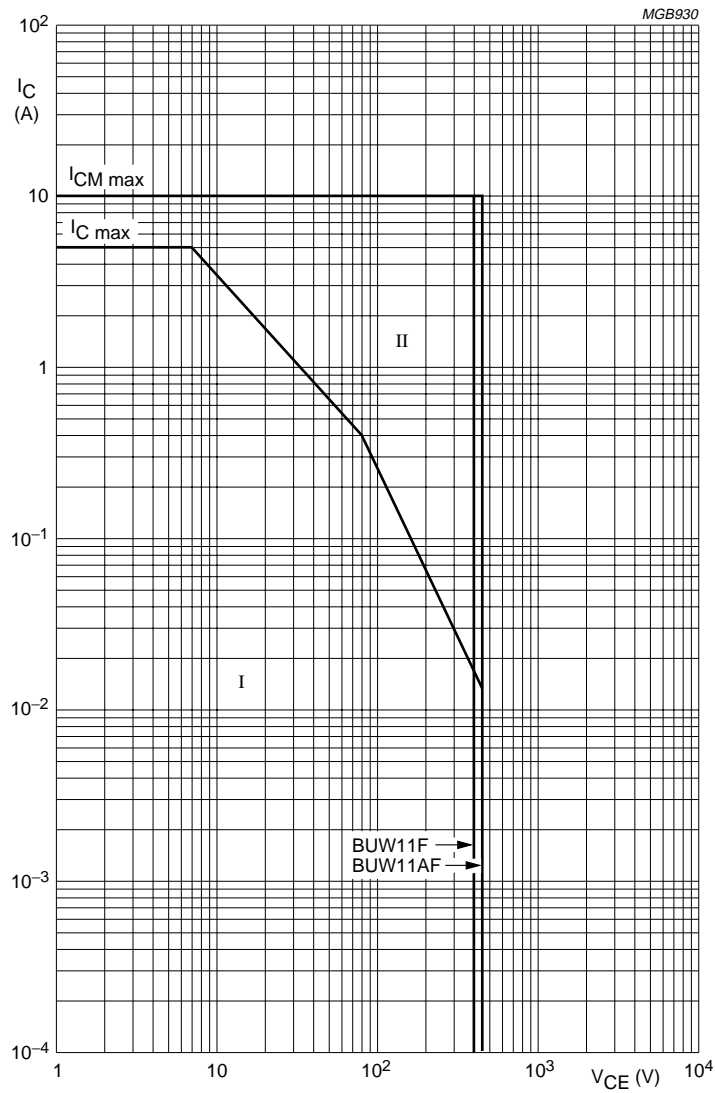
| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|--|---|---|------|------|------|---------------|
| $V_{CEOsust}$ | collector-emitter sustaining voltage BUW11F BUW11AF | $I_C = 100\text{ mA}$; $I_{Boff} = 0$; $L = 25\text{ mH}$; see Figs 5 and 6 | 400 | – | – | V |
| | | | 450 | – | – | V |
| V_{CEsat} | collector-emitter saturation voltage BUW11F BUW11AF | $I_C = 3\text{ A}$; $I_B = 600\text{ mA}$ | – | – | 1.5 | V |
| | | $I_C = 2.5\text{ A}$; $I_B = 500\text{ mA}$ | – | – | 1.5 | V |
| V_{BEsat} | base-emitter saturation voltage BUW11F BUW11AF | $I_C = 3\text{ A}$; $I_B = 600\text{ mA}$ | – | – | 1.4 | V |
| | | $I_C = 2.5\text{ A}$; $I_B = 500\text{ mA}$ | – | – | 1.4 | V |
| I_{Csat} | collector saturation current BUW11F BUW11AF | $V_{CE} = 1.5\text{ V}$ | – | – | 3 | A |
| | | | – | – | 2.5 | A |
| I_{CES} | collector-emitter cut-off current | $V_{CE} = V_{CESMmax}$; $V_{BE} = 0$; note 1 | – | – | 1 | mA |
| | | $V_{CE} = V_{CESMmax}$; $V_{BE} = 0$; $T_j = 125\text{ °C}$; note 1 | – | – | 2 | mA |
| I_{EBO} | emitter-base cut-off current | $V_{EB} = 9\text{ V}$; $I_C = 0$ | – | – | 10 | mA |
| h_{FE} | DC current gain | $V_{CE} = 5\text{ V}$; $I_C = 5\text{ mA}$; see Fig.7 | 10 | 18 | 35 | |
| | | $V_{CE} = 5\text{ V}$; $I_C = 0.5\text{ A}$; see Fig.7 | 10 | 20 | 35 | |
| Switching times resistive load (Figs 8 and 9) | | | | | | |
| t_{on} | turn-on time BUW11F BUW11AF | $I_{Con} = 3\text{ A}$; $I_{Bon} = -I_{Boff} = 600\text{ mA}$ | – | – | 1 | μs |
| | | $I_{Con} = 2.5\text{ A}$; $I_{Bon} = -I_{Boff} = 500\text{ mA}$ | – | – | 1 | μs |
| t_s | storage time BUW11F BUW11AF | $I_{Con} = 3\text{ A}$; $I_{Bon} = -I_{Boff} = 600\text{ mA}$ | – | – | 4 | μs |
| | | $I_{Con} = 2.5\text{ A}$; $I_{Bon} = -I_{Boff} = 500\text{ mA}$ | – | – | 4 | μs |
| t_f | fall time BUW11F BUW11AF | $I_{Con} = 3\text{ A}$; $I_{Bon} = -I_{Boff} = 600\text{ mA}$ | – | – | 0.8 | μs |
| | | $I_{Con} = 2.5\text{ A}$; $I_{Bon} = -I_{Boff} = 500\text{ mA}$ | – | – | 0.8 | μs |
| Switching times inductive load (Figs 10 and 11) | | | | | | |
| t_s | storage time BUW11F BUW11AF | $I_{Con} = 3\text{ A}$; $I_B = 600\text{ mA}$; $V_{CL} = 250\text{ V}$; $T_c = 100\text{ °C}$ | – | 2 | 2.5 | μs |
| | | $I_{Con} = 2.5\text{ A}$; $I_B = 500\text{ mA}$; $V_{CL} = 300\text{ V}$; $T_c = 100\text{ °C}$ | – | 2 | 2.5 | μs |
| t_f | fall time BUW11F BUW11AF | $I_{Con} = 3\text{ A}$; $I_B = 600\text{ mA}$; $V_{CL} = 250\text{ V}$; $T_c = 100\text{ °C}$ | – | 200 | 300 | ns |
| | | $I_{Con} = 2.5\text{ A}$; $I_B = 500\text{ mA}$; $V_{CL} = 300\text{ V}$; $T_c = 100\text{ °C}$ | – | 200 | 300 | ns |

Note

1. Measured with a half-sinewave voltage (curve tracer).

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Mounted **without** heatsink compound and 30 ± 5 N force on centre of package.

$T_{mb} < 25$ °C.

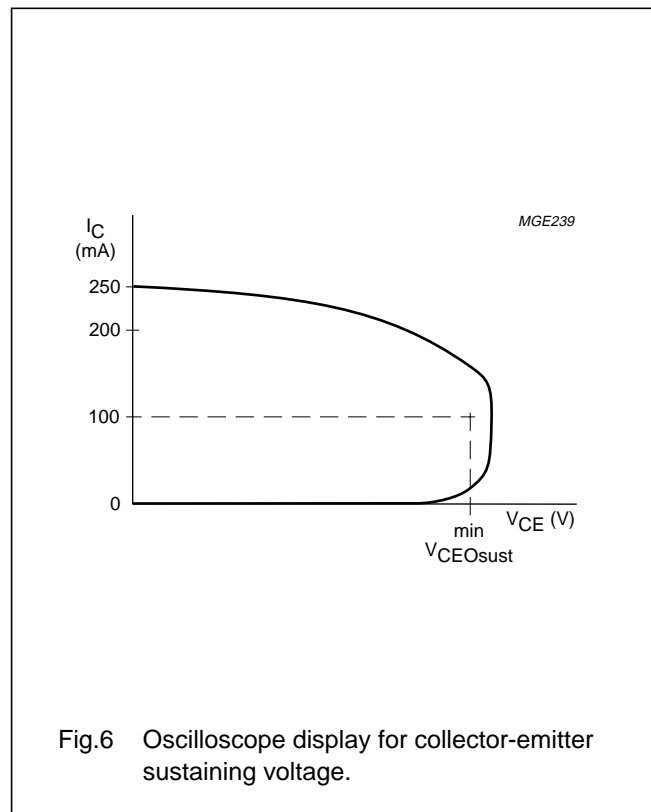
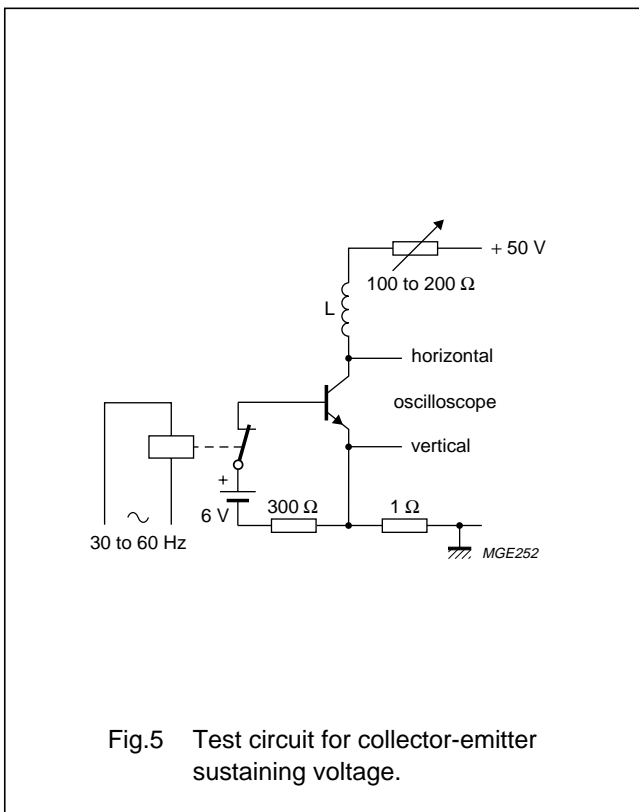
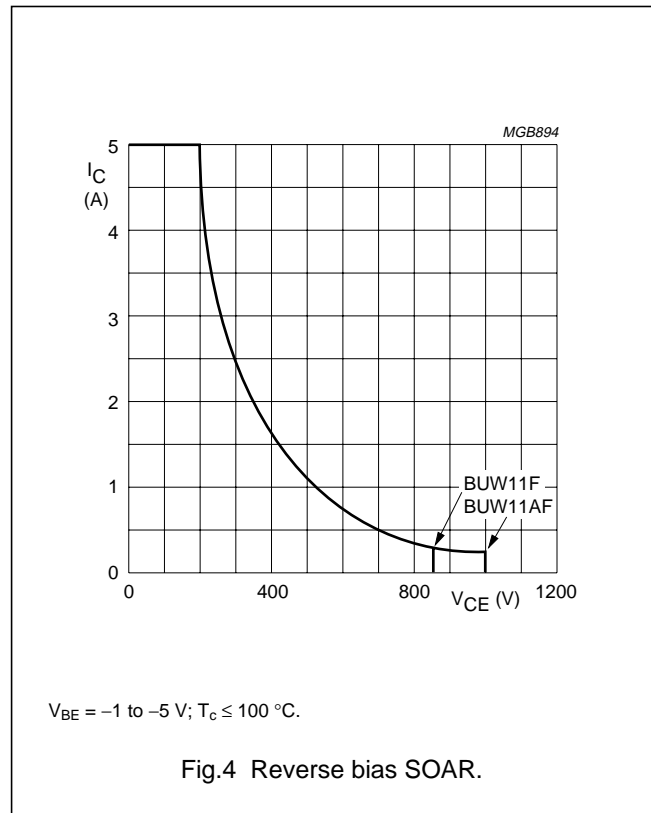
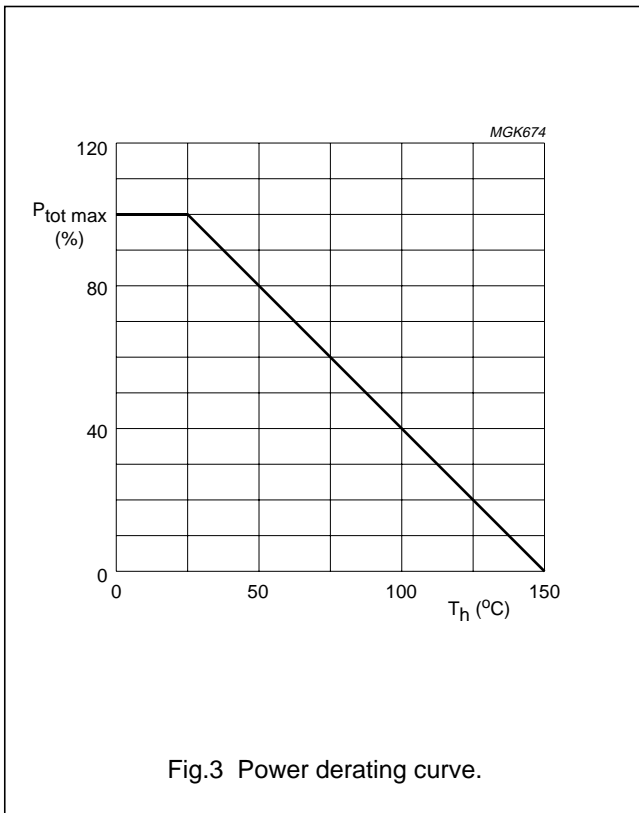
I - Region of permissible DC operation.

II - Permissible extension for repetitive pulse operation.

Fig.2 Forward bias SOAR.

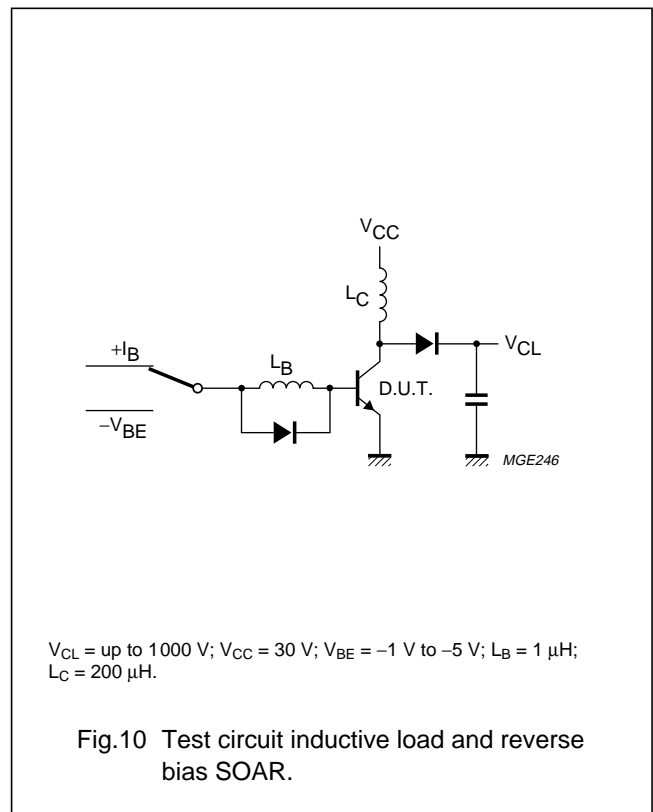
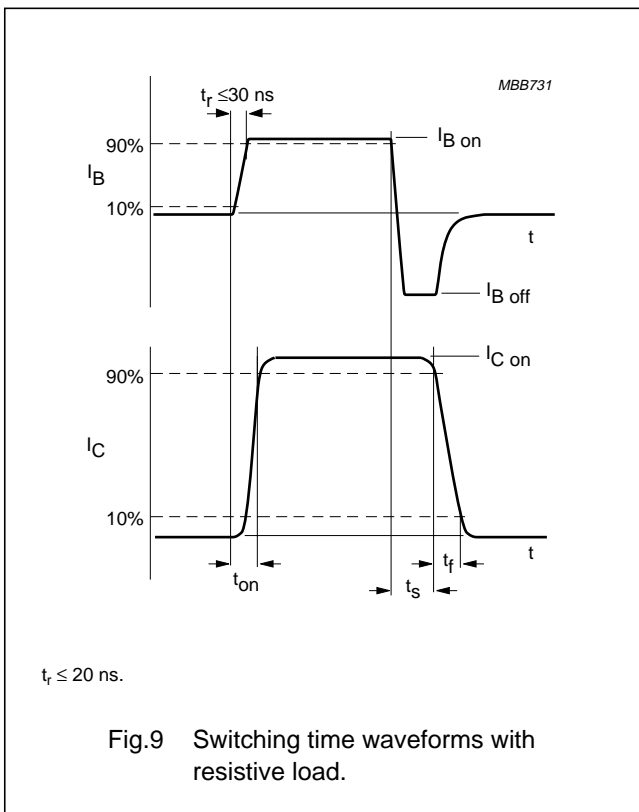
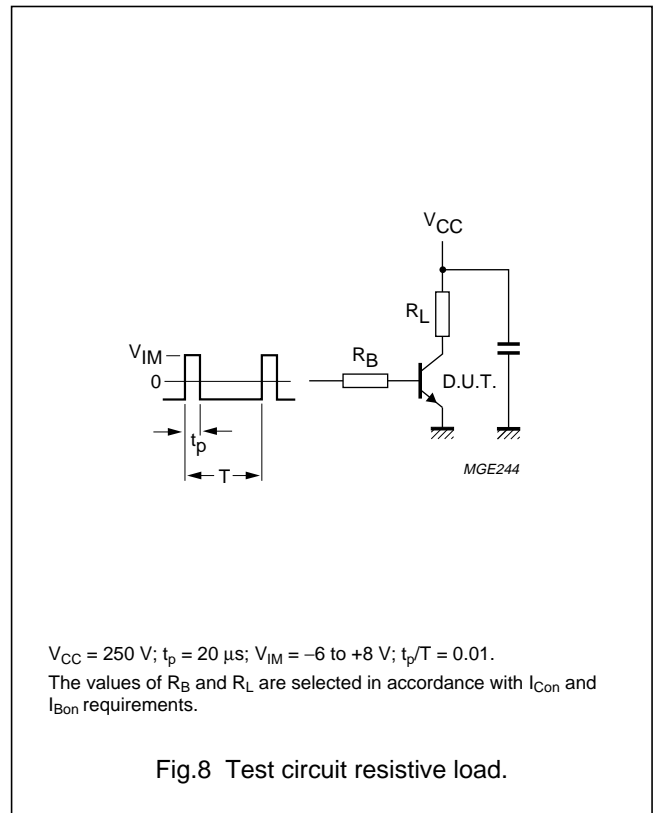
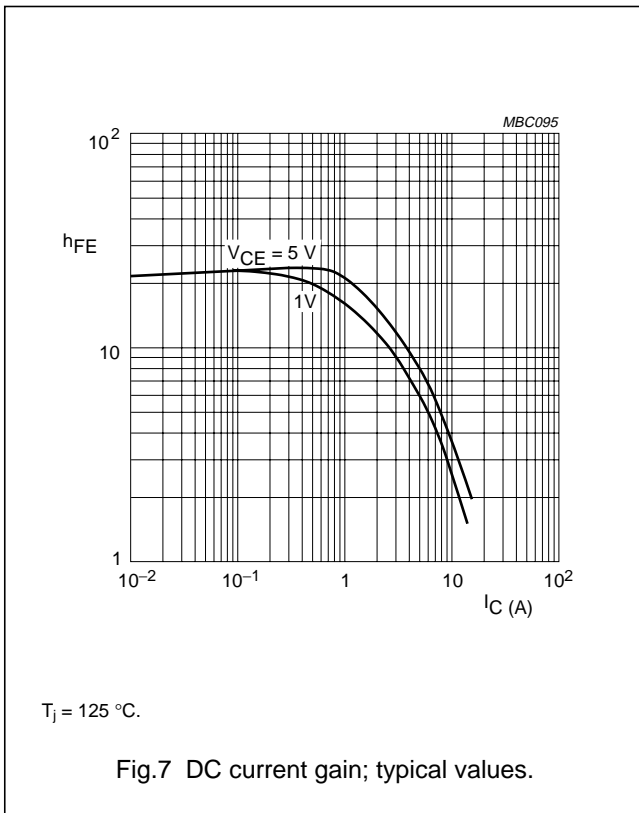
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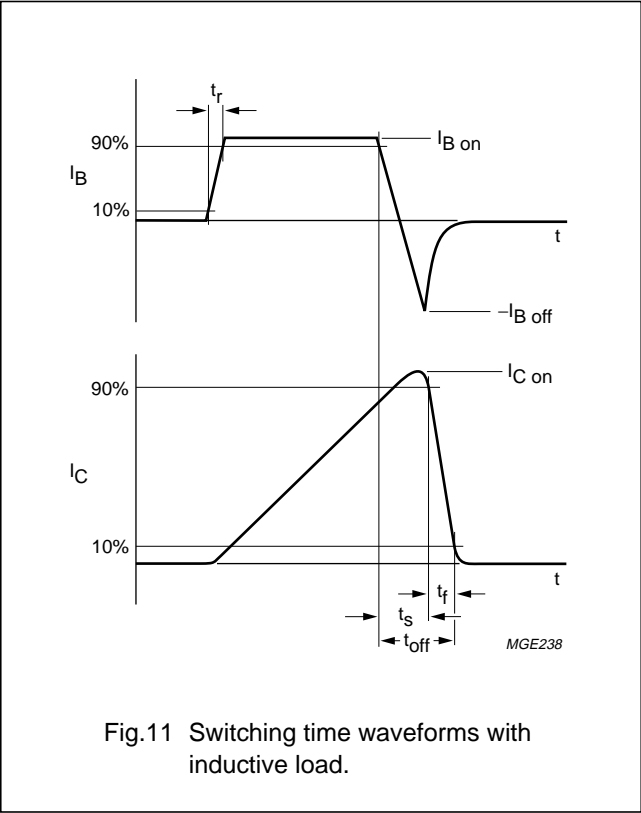


Fig.11 Switching time waveforms with inductive load.

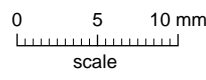
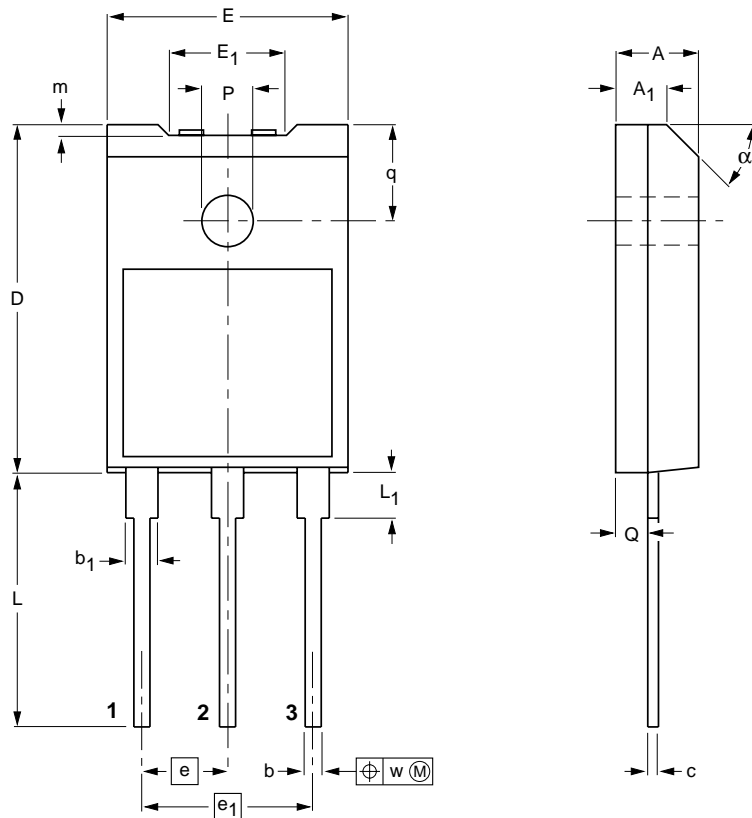
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PACKAGE OUTLINE

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3 leads (in-line)

SOT199



DIMENSIONS (mm are the original dimensions)

| UNIT | A | A ₁ | b | b ₁ | c | D | E | E ₁ | e | e ₁ | L | L ₁ ⁽¹⁾ | m | P | Q | q | w | α |
|------|------------|----------------|------------|----------------|------------|--------------|--------------|----------------|------|----------------|--------------|-------------------------------|------------|------------|------------|------------|-----|----------|
| mm | 5.2 4.8 | 3.4 3.0 | 1.2 1.0 | 2.1 1.9 | 0.6 0.5 | 21.5 20.5 | 15.3 14.7 | 7.8 6.8 | 5.45 | 10.9 | 16.5 15.7 | 3.7 3.3 | 0.8 0.6 | 3.3 3.1 | 2.1 1.9 | 6.2 5.8 | 0.4 | 45° |

Note

1. Terminals in this zone are not tinned.

| OUTLINE VERSION | REFERENCES | | | | EUROPEAN PROJECTION | ISSUE DATE |
|-----------------|------------|-------|------|--|---------------------|------------|
| | IEC | JEDEC | EIAJ | | | |
| SOT199 | | | | | | 97-06-27 |

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DEFINITIONS

| | |
|---|---|
| Data sheet status | |
| Objective specification | This data sheet contains target or goal specifications for product development. |
| Preliminary specification | This data sheet contains preliminary data; supplementary data may be published later. |
| Product specification | This data sheet contains final product specifications. |
| Limiting values | |
| Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability. | |
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Philips Semiconductors – a worldwide company

Argentina: see South America

Australia: 34 Waterloo Road, NORTH RYDE, NSW 2113,
Tel. +61 2 9805 4455, Fax. +61 2 9805 4466

Austria: Computerstr. 6, A-1101 WIEN, P.O. Box 213, Tel. +43 160 1010,
Fax. +43 160 101 1210

Belarus: Hotel Minsk Business Center, Bld. 3, r. 1211, Volodarski Str. 6,
220050 MINSK, Tel. +375 172 200 733, Fax. +375 172 200 773

Belgium: see The Netherlands

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Bulgaria: Philips Bulgaria Ltd., Energoproject, 15th floor,
51 James Bourchier Blvd., 1407 SOFIA,
Tel. +359 2 689 211, Fax. +359 2 689 102

Canada: PHILIPS SEMICONDUCTORS/COMPONENTS,
Tel. +1 800 234 7381

China/Hong Kong: 501 Hong Kong Industrial Technology Centre,
72 Tat Chee Avenue, Kowloon Tong, HONG KONG,
Tel. +852 2319 7888, Fax. +852 2319 7700

Colombia: see South America

Czech Republic: see Austria

Denmark: Prags Boulevard 80, PB 1919, DK-2300 COPENHAGEN S,
Tel. +45 32 88 2636, Fax. +45 31 57 0044

Finland: Sinikalliontie 3, FIN-02630 ESPOO,
Tel. +358 9 615800, Fax. +358 9 61580920

France: 4 Rue du Port-aux-Vins, BP317, 92156 SURESNES Cedex,
Tel. +33 1 40 99 6161, Fax. +33 1 40 99 6427

Germany: Hammerbrookstraße 69, D-20097 HAMBURG,
Tel. +49 40 23 53 60, Fax. +49 40 23 536 300

Greece: No. 15, 25th March Street, GR 17778 TAVROS/ATHENS,
Tel. +30 1 4894 339/239, Fax. +30 1 4814 240

Hungary: see Austria

India: Philips INDIA Ltd, Band Box Building, 2nd floor,
254-D, Dr. Annie Besant Road, Worli, MUMBAI 400 025,
Tel. +91 22 493 8541, Fax. +91 22 493 0966

Indonesia: see Singapore

Ireland: Newstead, Clonskeagh, DUBLIN 14,
Tel. +353 1 7640 000, Fax. +353 1 7640 200

Israel: RAPAC Electronics, 7 Kehilat Saloniki St, PO Box 18053,
TEL AVIV 61180, Tel. +972 3 645 0444, Fax. +972 3 649 1007

Italy: PHILIPS SEMICONDUCTORS, Piazza IV Novembre 3,
20124 MILANO, Tel. +39 2 6752 2531, Fax. +39 2 6752 2557

Japan: Philips Bldg 13-37, Kohnan 2-chome, Minato-ku, TOKYO 108,
Tel. +81 3 3740 5130, Fax. +81 3 3740 5077

Korea: Philips House, 260-199 Itaewon-dong, Yongsan-ku, SEOUL,
Tel. +82 2 709 1412, Fax. +82 2 709 1415

Malaysia: No. 76 Jalan Universiti, 46200 PETALING JAYA, SELANGOR,
Tel. +60 3 750 5214, Fax. +60 3 757 4880

Mexico: 5900 Gateway East, Suite 200, EL PASO, TEXAS 79905,
Tel. +9-5 800 234 7381

Middle East: see Italy

Netherlands: Postbus 90050, 5600 PB EINDHOVEN, Bldg. VB,
Tel. +31 40 27 82785, Fax. +31 40 27 88399

New Zealand: 2 Wagener Place, C.P.O. Box 1041, AUCKLAND,
Tel. +64 9 849 4160, Fax. +64 9 849 7811

Norway: Box 1, Manglerud 0612, OSLO,
Tel. +47 22 74 8000, Fax. +47 22 74 8341

Philippines: Philips Semiconductors Philippines Inc.,
106 Valero St. Salcedo Village, P.O. Box 2108 MCC, MAKATI,
Metro MANILA, Tel. +63 2 816 6380, Fax. +63 2 817 3474

Poland: Ul. Lukiska 10, PL 04-123 WARSZAWA,
Tel. +48 22 612 2831, Fax. +48 22 612 2327

Portugal: see Spain

Romania: see Italy

Russia: Philips Russia, Ul. Usatcheva 35A, 119048 MOSCOW,
Tel. +7 095 755 6918, Fax. +7 095 755 6919

Singapore: Lorong 1, Toa Payoh, SINGAPORE 1231,
Tel. +65 350 2538, Fax. +65 251 6500

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South Africa: S.A. PHILIPS Pty Ltd., 195-215 Main Road Martindale,
2092 JOHANNESBURG, P.O. Box 7430 Johannesburg 2000,
Tel. +27 11 470 5911, Fax. +27 11 470 5494

South America: Rua do Rocio 220, 5th floor, Suite 51,
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Tel. +55 11 821 2333, Fax. +55 11 829 1849

Spain: Balmes 22, 08007 BARCELONA,
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Sweden: Kottbygatan 7, Akalla, S-16485 STOCKHOLM,
Tel. +46 8 632 2000, Fax. +46 8 632 2745

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TAIPEI, Taiwan Tel. +886 2 2134 2865, Fax. +886 2 2134 2874

Thailand: PHILIPS ELECTRONICS (THAILAND) Ltd.,
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Tel. +66 2 745 4090, Fax. +66 2 398 0793

Turkey: Talatpasa Cad. No. 5, 80640 GÜLTEPE/ISTANBUL,
Tel. +90 212 279 2770, Fax. +90 212 282 6707

Ukraine: PHILIPS UKRAINE, 4 Patrice Lumumba str., Building B, Floor 7,
252042 KIEV, Tel. +380 44 264 2776, Fax. +380 44 268 0461

United Kingdom: Philips Semiconductors Ltd., 276 Bath Road, Hayes,
MIDDLESEX UB3 5BX, Tel. +44 181 730 5000, Fax. +44 181 754 8421

United States: 811 East Arques Avenue, SUNNYVALE, CA 94088-3409,
Tel. +1 800 234 7381

Uruguay: see South America

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Printed in The Netherlands

137067/00/01/pp12

Date of release: 1997 Aug 14

Document order number: 9397 750 02718

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